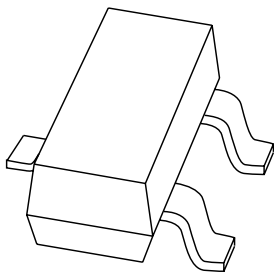


DATA SHEET



PBSS5240T

40 V, 2 A

PNP low V_{CEsat} (BISS) transistor

Product data sheet
Supersedes data of 2001 Oct 31

2004 Jan 15

40 V, 2 A

PNP low V_{CEsat} (BISS) transistor

PBSS5240T

FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- Replacement for SOT89/SOT223 standard packaged transistor.

APPLICATIONS

- Supply line switching circuits
- Battery management applications
- DC/DC converter applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

DESCRIPTION

PNP low V_{CEsat} transistor in a SOT23 plastic package.
NPN complement: PBSS4240T.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PBSS5240T	ZF*

Note

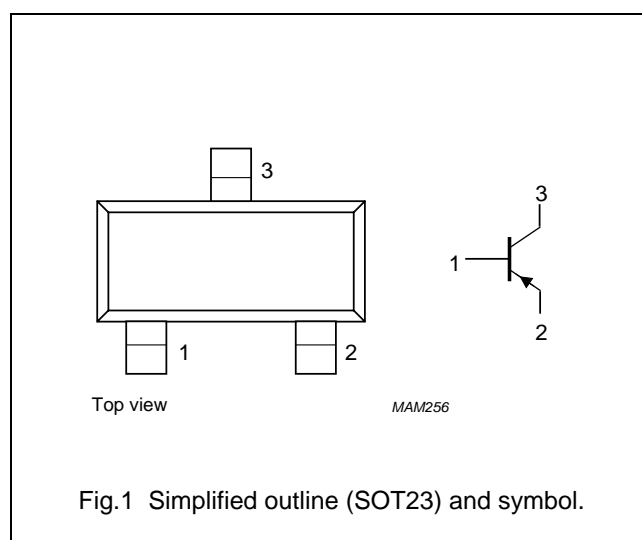
- * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	-40	V
I_C	collector current (DC)	-2	A
I_{CM}	peak collector current	-3	A
R_{CEsat}	equivalent on-resistance	<220	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS5240T	—	plastic surface mounted package; 3 leads	SOT23

40 V, 2 A
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PBSS5240T

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–40	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–2	A
I_{CM}	peak collector current		–	–3	A
I_{BM}	peak base current		–	–300	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	300	mW
		$T_{amb} \leq 25\text{ °C}$; note 2	–	480	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Device mounted on a printed-circuit board, single sided copper, tin plated, standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tin plated, mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

Notes

1. Device mounted on a printed-circuit board, single sided copper, tin plated, standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tin plated, mounting pad for collector 1 cm².

40 V, 2 A
PNP low V_{CEsat} (BISS) transistor

PBSS5240T

CHARACTERISTICS $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

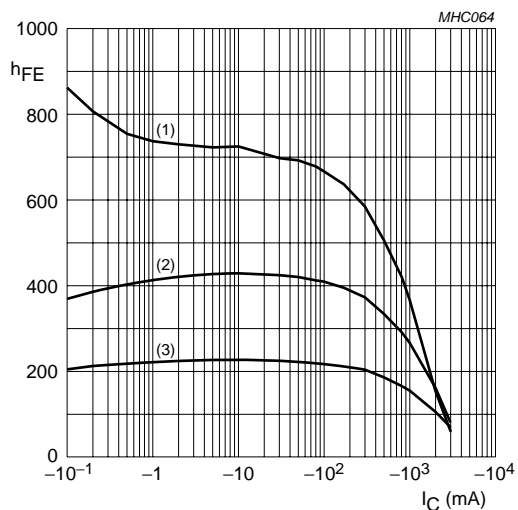
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0$	–	–	–100	nA
		$V_{CB} = -30\text{ V}; I_E = 0; T_J = 150\text{ }^{\circ}\text{C}$	–	–	–50	μA
I_{BEO}	emitter-base cut-off current	$V_{EB} = -4\text{ V}; I_C = 0$	–	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -2\text{ V}$				
		$I_C = -100\text{ mA}$	300	450	–	
		$I_C = -500\text{ mA}$	260	350	–	
		$I_C = -1\text{ A}$	210	290	–	
		$I_C = -2\text{ A}$	100	180	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	–	–55	–100	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–70	–110	mV
		$I_C = -750\text{ mA}; I_B = -15\text{ mA}$	–	–140	–225	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–140	–225	mV
		$I_C = -2\text{ A}; I_B = -200\text{ mA}$	–	–240	–350	mV
R_{CEsat}	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA};$ note 1	–	160	<220	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = -2\text{ A}; I_B = -200\text{ mA}$	–	–	–1.1	V
$V_{BE(on)}$	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -100\text{ mA}$	–	–	–0.75	V
f_T	transition frequency	$I_C = -100\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}$	100	200	–	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0;$ $f = 1\text{ MHz}$	–	23	28	pF

Note

1. Device mounted on a printed-circuit board, single sided copper, tin plated, standard footprint.

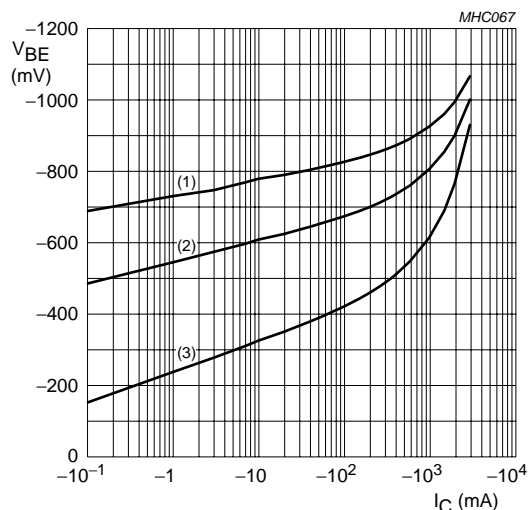
40 V, 2 A
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PBSS5240T

 $V_{CE} = -2V$.

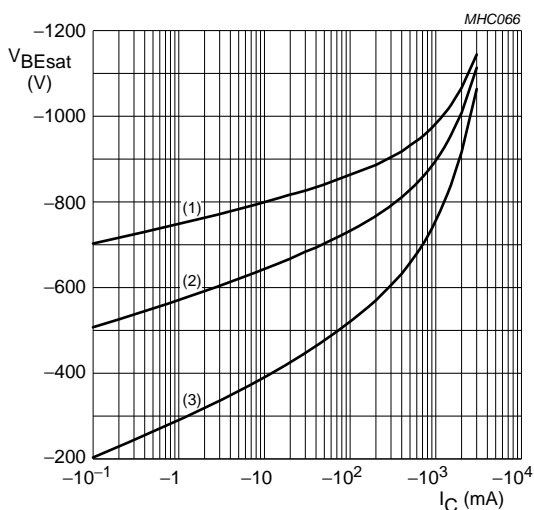
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$.

Fig.2 DC current gain as a function of collector current; typical values.

 $V_{CE} = -2V$.

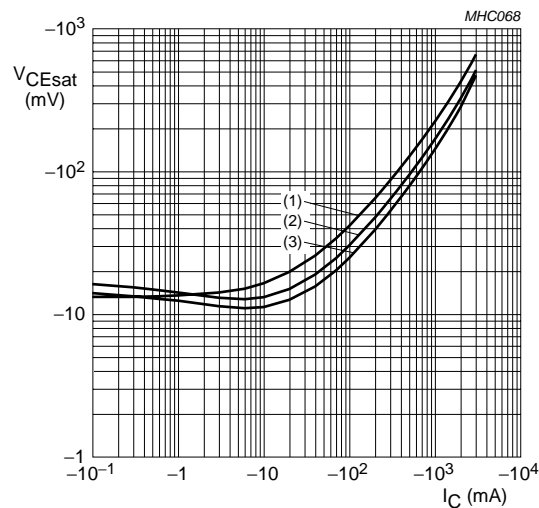
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$.
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
(3) $T_{amb} = 150\text{ }^{\circ}\text{C}$.

Fig.3 Base-emitter voltage as a function of collector current; typical values.

 $I_C/I_B = 20$.

- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$.
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
(3) $T_{amb} = 150\text{ }^{\circ}\text{C}$.

Fig.4 Base-emitter saturation voltage as a function of collector current; typical values.

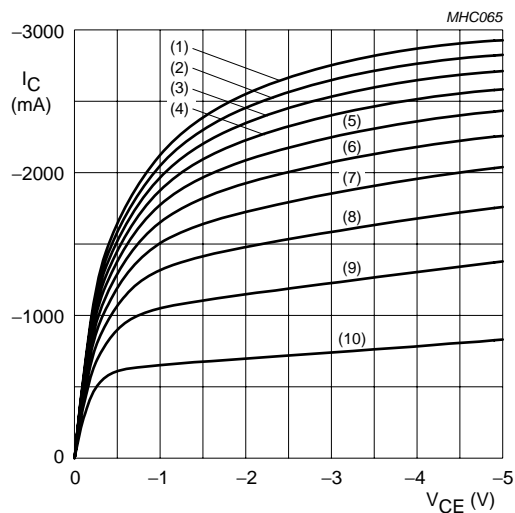
 $I_C/I_B = 20$.

- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$.

Fig.5 Collector-emitter saturation voltage as a function of collector current; typical values.

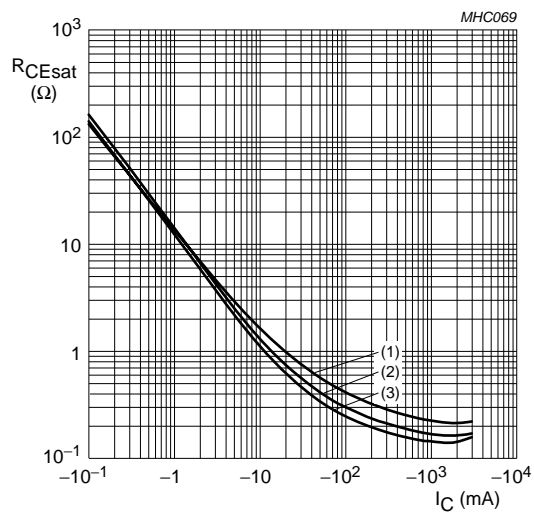
40 V, 2 A
PNP low V_{CEsat} (BISS) transistor

PBSS5240T



- (1) $I_B = -23.0$ mA. (5) $I_B = -13.8$ mA. (8) $I_B = -6.9$ mA.
 (2) $I_B = -20.7$ mA. (6) $I_B = -11.5$ mA. (9) $I_B = -4.6$ mA.
 (3) $I_B = -18.4$ mA. (7) $I_B = -9.2$ mA. (10) $I_B = -2.3$ mA.
 (4) $I_B = -16.1$ mA.

Fig.6 Collector current as a function of collector-emitter voltage; typical values.



- $I_C/I_B = 20$.
 (1) $T_{amb} = 150$ °C.
 (2) $T_{amb} = 25$ °C.
 (3) $T_{amb} = -55$ °C.

Fig.7 Equivalent on-resistance as a function of collector current; typical values.

40 V, 2 A

PNP low V_{CEsat} (BISS) transistor

PBSS5240T

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23

The diagrams illustrate the SOT23 package dimensions. The top view shows the overall width D and lead spacing e. The side view shows the maximum height A, lead height A1, and lead thickness c. The bottom view shows the lead pitch e1 and the distance from the lead center to the package edge b_p. A detail X shows the lead profile with dimensions L_p and Q. A scale bar indicates 0 to 2 mm.

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				<div> <div>04-11-04</div> <div>06-03-16</div> </div>

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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